

Electronic Acknowledgement Receipt

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International Application Number:	
Confirmation Number:	3451
Title of Invention:	Method for Self-Supported Transfer of a Fine Layer by Pulsation after Implantation or Co-Implantation
First Named Inventor/Applicant Name:	Nguyet-Phuong Nguyen
Customer Number:	90678
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Filer Authorized By:	Jasper W. Dockrey
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Aspar_et_al_1996_99-111.pdf	386796 <small>e8b6c18d2b60098118a24842677a1f02439e</small>	no	7

Warnings:

Information:

2	NPL Documents	Aspar_et_al_1996_1985-1986.pdf	80682 4807811e30c01c1cd19d9c3196a61c63b54e9f	no	2
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3	NPL Documents	Aspar_et_al_1997_233-240.pdf	440138 54297eba08ed9913c1f86c5ecc7305a712b5a0d	no	8
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4	NPL Documents	Aspar_et_al_2001_834-840.pdf	675066 913b0c0e1888c5d9fed672fed95e162d17c8511d	no	8
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5	NPL Documents	Auberton-Herve.pdf	983663 24ee9669e146513e1f8a093808b1d457632d35f	no	16
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6	NPL Documents	Auberton-Herve_A_J_et_al_A_New_Sal_Material.pdf	272862 1752b70bc73946a1cc955de0ca2d16795c5d6605	no	6
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7	NPL Documents	Auberton-Herve_A_J_et_al_SOI_Materials_for_ULSI_Applications.pdf	594763 63b048edcca102db657c42ac03cc0809875a3d1	no	5
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8	NPL Documents	Ayguavives_et_al.pdf	277991 715ba6d1223212ac96071c17100c7b3dc160d505	no	4
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9	NPL Documents	Blanchard-Lagahae-C-Hydrogen-and-Helium.pdf	584601 9c86b10b428dcb700135d28d08c19c94b5f031	no	13
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10	NPL Documents	Bloch_et_al.pdf	290290 647bf785114d3c2503d0a62943d0e513b3e77a0d	no	4
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11	NPL Documents	Borgatti_Stephen_The_Root-Mean_Square.pdf	44565 6f4bdeaf8fc9565ba748b5a5756ad74c8f44b577	no	1
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12	NPL Documents	Bruel_et_al_1997_1636-1641.pdf	374214 a02eb9f98b1c4a78ade35c4eb6c57f41279a721f	no	6
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13	NPL Documents	Bruel_M_Silicon_on_Insulator_Material.pdf	118402 025ebdfe641349c17f185ca8b461128605d97a	no	2
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14	NPL Documents	Bruel_M_Silicon_on_insulator_material_technology.pdf	123231 0901c5f8edc1d8d1c7f28ab699942f11319e4eb	no	2
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15	NPL Documents	Bruel_M_Smart_Cut_A_New_SOI_Material_Technology.pdf	2170085 2b80c4b136c26ab8c7e76750e9731bf17c5886e	no	25
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16	NPL Documents	Bruel_M_Smart_Cut_A_Promising_New_SOI.pdf	122154 f672c0c4f9b125c55a79c93928a763c36ef76d0	no	2
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18	NPL Documents	Bruel_Michel_Application_of_Hydrogen_on_Beams_to_Silicon.pdf	483916 d452908bc824ccc3288a7cd44748958c663db1d	no	7
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19	NPL Documents	Canham_et_al.pdf	217996 ea015d8ee042c438b3c42a79f0143c929443280	no	5
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20	NPL Documents	Carter_G_et_al_The_Collection_of_Ions_Implanted_in_Semiconductors_IL.pdf	669972 318947B0496c5a661b596b56823a6518015b5408	no	8
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21	NPL Documents	Carter-et-al-Applications-of-Ion-Beams-To-Materials.PDF	600857 2313e45398c3c30003803d6bcb24b42bb62	no	13
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22	NPL Documents	Cassidy-Victor-M-Ion-Implantation_Process_Toughens_Metalworking.pdf	195180 448ee92241c1b1864a7f10d29ab8131201b70e	no	3
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23	NPL Documents	Cerofolini_et_al_1992.pdf	674531 bf6c56a2af65d07e2e44839283105d5a55aef4363	no	10
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24	NPL Documents	Cerofolini_et_al_2000.PDF	2728185 d2e59f13db82283a8f8e303ef99533d035c9ba0	no	52
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25	NPL Documents	Chu_Ion-Implantation_In_Semiconductors.PDF	499300 99886882ac09449457f10540047e8f05595bec	no	12
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26	NPL Documents	Chu_PK_Plasma-Immersion_Ion-Implantation.pdf	245084 80a176150a778a2735bab9648cb795e24cc2797	no	5
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27	NPL Documents	Chu_WK_et_al_Radiation_Damage_of_50-250_keV_Hydrogen.pdf	663443 55f76ca209ab8bdc5d6d9f8eaa79693a0ad3d73a15	no	10
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32	NPL Documents	Denteneer_et_al_1989_979-984.pdf	299205 9a1bc7616268c450c107910a24c1956c759c6bba	no	5
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33	NPL Documents	Denteneer_et_al_1989_1884-1887.pdf	342276 a91f56edf7086a9e7d6c3c62827a65ec124ba	no	4
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34	NPL Documents	DiCioccio_et_al_1996.pdf	130526 0f566678fbb26c45d975574c99b298932ac4	no	2
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35	NPL Documents	Diem_et_al.pdf	846924 149415ab77ced3f9cd8105d2a8ac0e832d999ca	no	10
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36	NPL Documents	Dirks_et_al.pdf	1187199 d408b5560b3cbe538faaa781ca71ec23e786b	no	15
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38	NPL Documents	Duo_et_al_2001_477-482.pdf	821079 6539e4d26a7baed37c9d5483b517ddcab7e8d2d	no	6
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39	NPL Documents	Duo_et_al_2001_3780-3786.PDF	549396 0e37d771d8874bdc45d4ba1078f36ae903f2d1a	no	6
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40	NPL Documents	DiCioccio_et_al_1997.pdf	744238 17d96a785c7a09bb5dc5278e6b5a18c3d44b090c	no	8
Warnings:					
Information:					
Total Files Size (in bytes):			24467800		
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p><u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p><u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p><u>New International Application Filed with the USPTO as a Receiving Office</u> If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					